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U	I	Investor	Document ID	Issue Date	Page	Title	Current RR	Current IRR
1	□	AHN, KY et al	US 20050028695 A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrically shaped metal node		
2	□	AHN, KY et al	US 20050028603 A	20050203	32	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrically shaped metal node		
3	□	AHN, KY et al	US 20050028602 A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate separated from floating gate by asymmetrically shaped metal node		
4	□	AHN, KY et al	US 20030048666 A	20030318	39	Floating gate transistor for memory array used in programmable logic array, comprises control gate and floating gate, and is separated from floating gate		
5	□	AHN, KY et al	US 20030042527 A	20030306	38	Depletion mode floating gate transistor for flash memory, has control gate separated from floating gate by asymmetrically shaped metal node made low tunnel barrier		
6	□	CHE, Y et al	CN 1527099 A	20040808	NA	Setting method and device for surface ion body induced photon resonance tunnelling type one-dimensional photonic band gap structure		
7	□	Higashit, Hitoshi	US 5848559 A	19970708	24	Single-electron tunnelling logic device	326/136	257/31; 257/E28.822;
8	□	MARKS, A M	EP 172464 A	19960226	33	Femto diode and applications - has sub-micron metal cylinder with asymmetric tunnel junction and reflecting step		
9	□	Marks; Almn M.	US 5268258 A	19931207	18	Monomolecular resist and process for beamwriter	430/286	
10	□	Marks; Almn M.	US 4972084 A	19901120	15	Lighting devices with quantum electric/light power converters	307/150	257/88; 257/E26.02;